

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1 - 14 (Cancelled)

Claim 15 (Currently amended): ~~The gas-feeding device according to claim 14 wherein said plurality of holes are gradient holes.~~

A gas-feeding device for feeding gas into a film-forming apparatus having an inner part and an outer part, comprising:

a gas-feeding pipe partially mounted between the inner part and the outer part for adjusting gas flowing therein in the direction toward a wall of the outer part wherein the gas-feeding pipe has a plurality of holes with their size varying regularly from down to top.

Claim 16 (Currently amended): ~~A method for feeding a gas into a film into a film-forming apparatus having an inner part and an outer part to form a film on a wafer mounted in said inner part in a semiconductor process said inner part being hotter than said outer part comprising steps of:~~

(a) ~~feeding said gas into a space between said cooler outer part and said hotter inner part, and directing a flow of said gas in a direction toward said cooler outer part in order to prevent particles adhered to said hotter inner part from peeling off; and~~

(b) ~~leading said gas into said inner part along a path between said outer part and said inner part so that said gas warms before reaching said hotter inner part.~~

A gas-feeding device for feeding gas into a space of a film-forming apparatus having an inner part and an outer part, wherein the space is located between the inner part and the outer part, comprising:

a gas-feeding pipe partially mounted between the inner part and the outer part for adjusting gas flowing therein in the direction toward a wall of the outer part wherein the gas-feeding pipe has an exit, the exit having the normal vector pointing to the outer part.

Claim 17 (Cancelled)

Claim 18 (Withdrawn): A method for feeding a gas into a film-forming apparatus having an inner part and an outer part to form a film on a wafer mounted in said inner part in a semiconductor process, comprising steps of:

(a) feeding said gas into a space between said outer part and said inner part and directing a flow of said gas in the direction toward a vertical wall of said outer part to prevent particles adhered to said inner part from peeling off; and

(b) leading said gas into said inner part along a path between said outer part and said inner part so that said gas warms before reaching said inner part.

Claim 19 (Withdrawn): The method according to claim 18 wherein said semiconductor process is one of a chemical vapor deposition process and a physical vapor deposition process.

Claim 20 (Withdrawn): The method according to claim 19 wherein said film is a silicon nitride film and said particles are  $\text{Si}_x\text{N}_4$  compounds.

Claim 21 (Withdrawn): The method according to claim 20 wherein said process includes steps of:

(c) controlling the temperature in said inner part of said film-forming apparatus in the range of  $600^\circ\text{C}$  to  $850^\circ\text{C}$ ; and

(d) controlling the pressure in said inner part of said film-forming apparatus in the range of 0.1 torr to 1 torr.

Claim 22 (Withdrawn): The method according to claim 20 wherein said gas is a purge gas selected from a group consisting of nitrogen, argon, and other inert gases.

Claim 23 (Withdrawn): The method according to claim 22 wherein after said film is formed, said process further includes a step of (e) controlling the flow rate of said gas in the range of 300 sccm to 2000 sccm for 5 min to 15 min to devacuum said film-forming apparatus.

Claim 24 (New): The gas-feeding device according to claim 15 wherein the gas-feeding device further comprises a controller connected to the gas-feeding pipe for controlling a flow rate of gas.

Claim 25 (New): The gas-feeding device according to claim 16 wherein the gas-feeding device further comprises a controller connected to the gas-feeding pipe for controlling a flow rate of gas.